

## Silicon Planar PIN Diode

### DESCRIPTION

The **MPND4005-0402** is designed for microwave applications.

### FEATURES

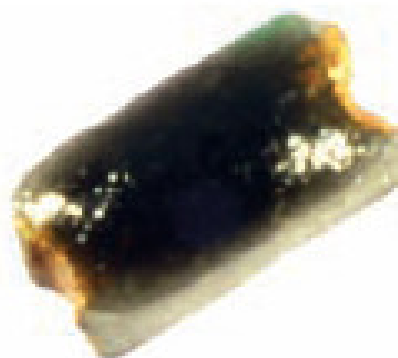
- Rugged construction
- Oxide/Nitride/Polyamide Passivation

### MAXIMUM RATINGS

RATING	LIMITS	UNITS
V <sub>r</sub>	100	V
P <sub>d</sub>	250mW, derate linearly to zero at T <sub>a</sub> =150°C	
T <sub>op</sub>	-65 to 150	°C
T <sub>stg</sub>	-65 to 150	°C

### PACKAGE STYLE

0402



### ELECTRICAL CHARACTERISTICS T<sub>c</sub>=25°C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I <sub>R</sub>	V <sub>R</sub> =30V	---	---	100	nA
V <sub>BR</sub>	I <sub>r</sub> =10uA	100	---	---	V
V <sub>F</sub>	I <sub>F</sub> =18mA	---	---	1000	mV
R <sub>S</sub>	I <sub>F</sub> =20mA, 3GHz	---	---	6.5	ohms
TL	I <sub>F</sub> =10mA, I <sub>R</sub> =6mA, 50% recovery	---	125	---	nS
C	V <sub>R</sub> =10V, F=1MHz	---	---	0.15	pF

## PACKAGE OUTLINE

0402-1

